

IN THE CLAIMS

Cancel claims 65 and 67-70.

Please substitute the following amended claim for a corresponding claim previously presented. A copy of the amended claim showing current revisions is attached.

71. (Amended) A nitride semiconductor light-emitting device comprising:

B<sup>1</sup> a first n-type clad layer comprising an n-type nitride semiconductor containing indium and gallium;

a first p-type clad layer comprising a p-type nitride semiconductor containing indium and gallium;

an active layer provided between said first n-type and p-type clad layers and having a multi-quantum well structure including a well layer comprising a nitride semiconductor represented by  $\text{In}_x\text{Ga}_{1-x}\text{N}$ , where  $0 < x < 1$ , and a barrier layer comprising a nitride semiconductor represented by  $\text{In}_y\text{Ga}_{1-y}\text{N}$ , where  $0 \leq y < 1$ ;

a second n-type clad layer comprising an n-type nitride semiconductor containing aluminum and gallium, said second n-type clad layer having a larger band gap than said first n-type clad layer, said second n-type clad layer being provided over said first n-type clad layer; and

a second p-type clad layer comprising a p-type nitride semiconductor containing aluminum and gallium, said second p-type clad layer having a larger band gap than said first p-type clad layer, and said second p-type clad layer being provided over said first p-type clad layer.